

FDS8882

N-Channel PowerTrench® MOSFET

30 V, 9 A, 20.0 mΩ

Features

- Max $r_{DS(on)}$ = 20.0 mΩ at $V_{GS} = 10$ V, $I_D = 9$ A
- Max $r_{DS(on)}$ = 22.5 mΩ at $V_{GS} = 4.5$ V, $I_D = 8$ A
- High performance trench technology for extremely low $r_{DS(on)}$ and fast switching
- High power and current handling capability
- Termination is Lead-free and RoHS Compliant

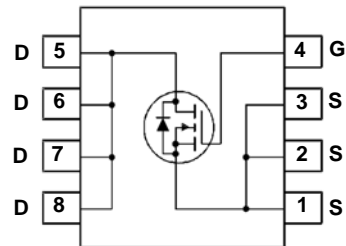
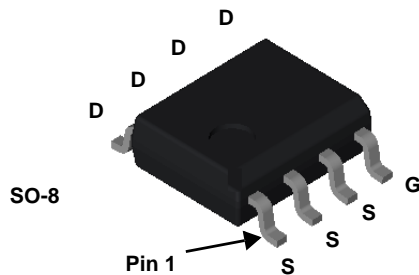


General Description

The FDS8882 has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance.

Applications

- Notebook System Regulators
- DC/DC Converters



MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous	9	A
	-Pulsed	21	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	32	mJ
P_D	Power Dissipation $T_A = 25$ °C (Note 1a)	2.5	W
	Power Dissipation $T_A = 25$ °C (Note 1b)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	25	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS8882	FDS8882	SO8	13 "	12 mm	2500 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		4		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-6		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 9\text{ A}$		13.2	20.0	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 8\text{ A}$		16.6	22.5	
		$V_{GS} = 10\text{ V}$, $I_D = 9\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		18.5	28.0	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 9\text{ A}$		36		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		707	940	pF
C_{oss}	Output Capacitance			138	185	pF
C_{rss}	Reverse Transfer Capacitance			88	135	pF
R_g	Gate Resistance			1.8		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		7	14	ns
t_r	Rise Time			3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	35	ns
t_f	Fall Time			4	10	ns
Q_g	Total Gate Charge		$V_{GS} = 0\text{ V to } 10\text{ V}$	$V_{DD} = 15\text{ V}$, $I_D = 9\text{ A}$	14	20
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to } 5\text{ V}$	8		11	nC
Q_{gs}	Gate to Source Charge		2.2			nC
Q_{gd}	Gate to Drain "Miller" Charge		2.8			nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 9\text{ A}$		0.8	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = 2.1\text{ A}$		0.7	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		17	31	ns
Q_{rr}	Reverse Recovery Charge			6	12	nC

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad of 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $50\text{ }^\circ\text{C/W}$ when mounted on a 1 in^2 pad of 2 oz copper.



b) $125\text{ }^\circ\text{C/W}$ when mounted on a minimum pad.

- Pulse Test: Pulse Width $< 300\text{ }\mu\text{s}$, Duty cycle $< 2.0\%$.
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 1\text{ mH}$, $I_{AS} = 8\text{ A}$, $V_{DD} = 27\text{ V}$, $V_{GS} = 10\text{ V}$.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

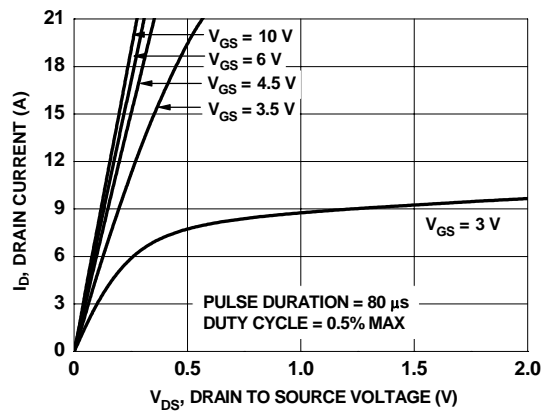


Figure 1. On Region Characteristics

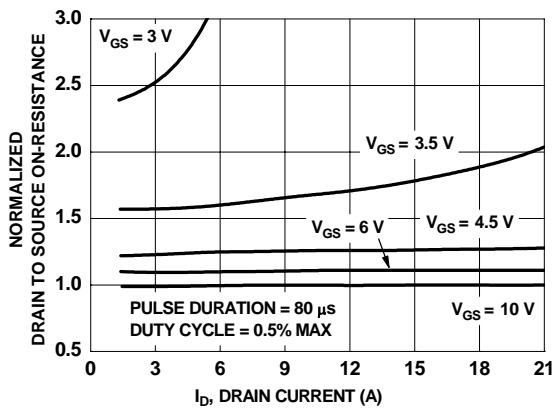


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

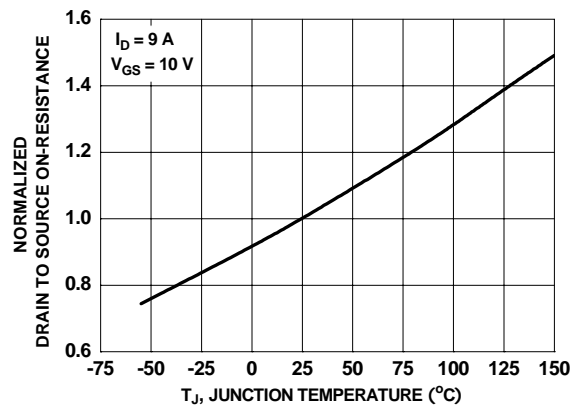


Figure 3. Normalized On Resistance vs Junction Temperature

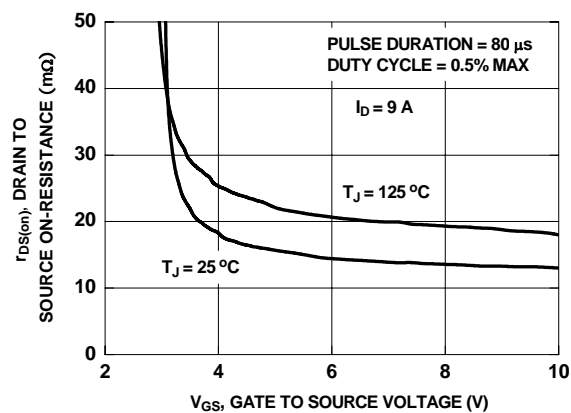


Figure 4. On-Resistance vs Gate to Source Voltage

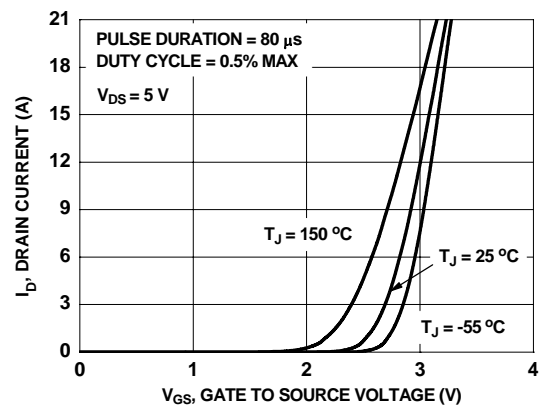


Figure 5. Transfer Characteristics

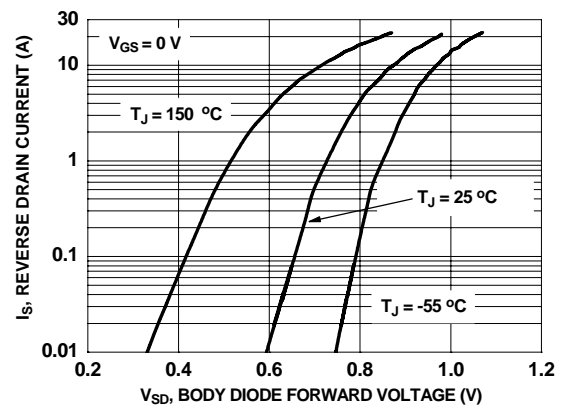


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

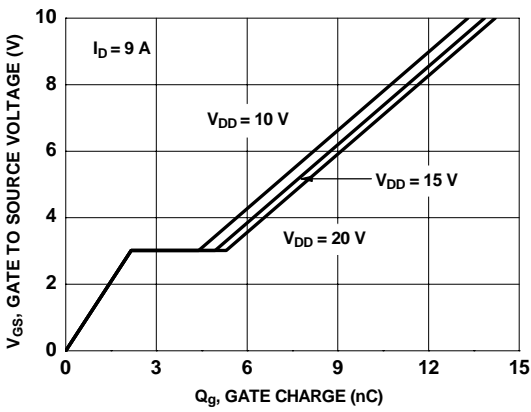


Figure 7. Gate Charge Characteristics

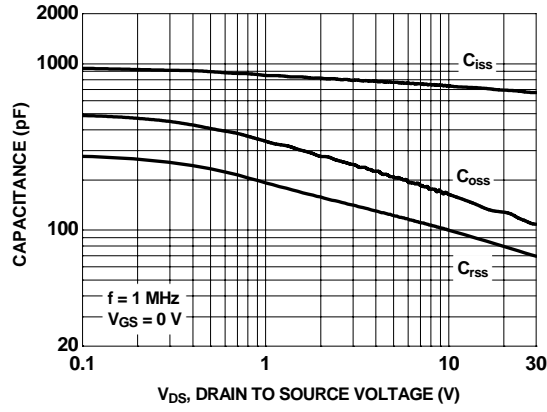


Figure 8. Capacitance vs Drain to Source Voltage

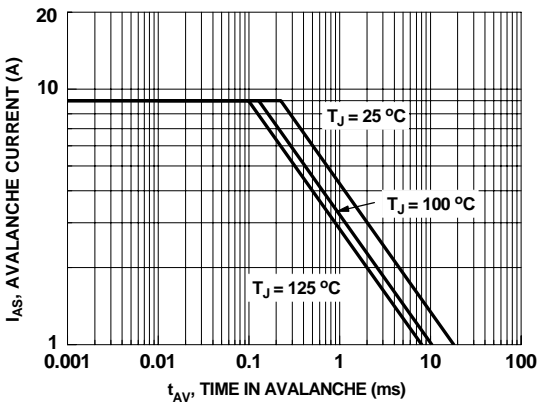


Figure 9. Unclamped Inductive Switching Capability

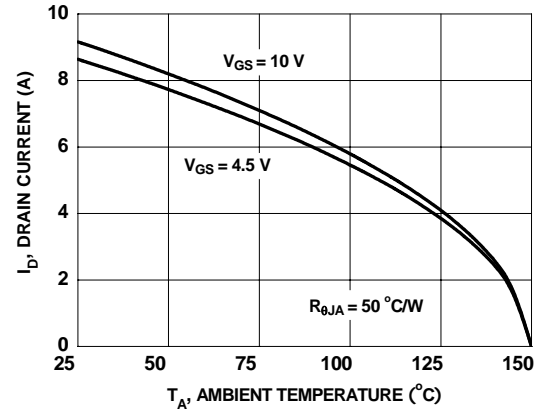


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

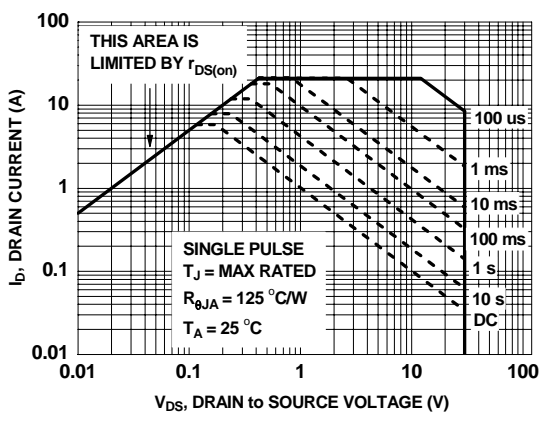


Figure 11. Forward Bias Safe Operating Area

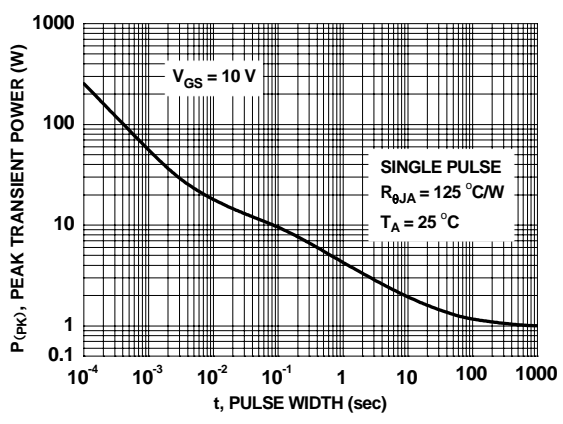


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

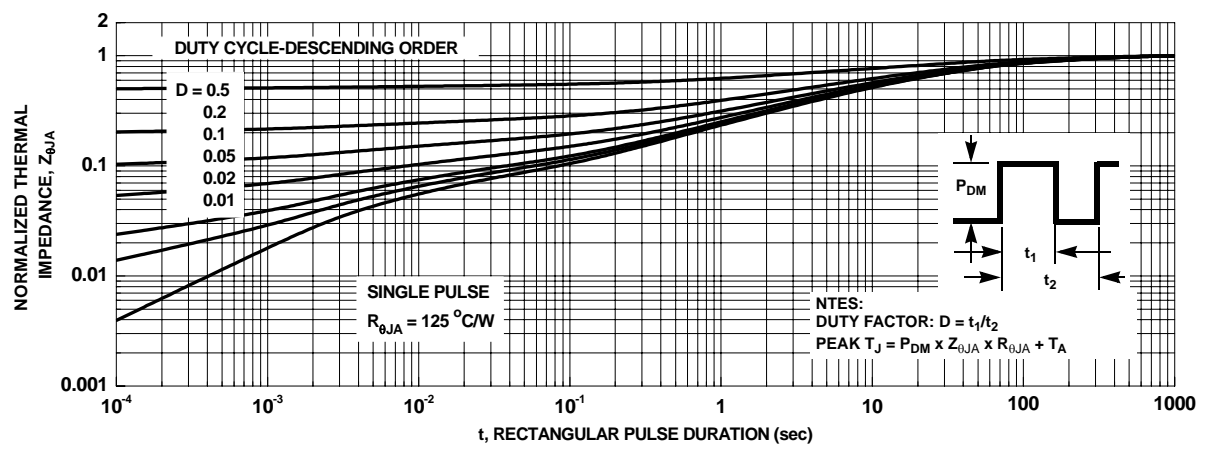








Figure 13. Junction-to-Ambient Transient Thermal Response Curve



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